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NTE125 General Purpose Silicon Rectifier

Description:

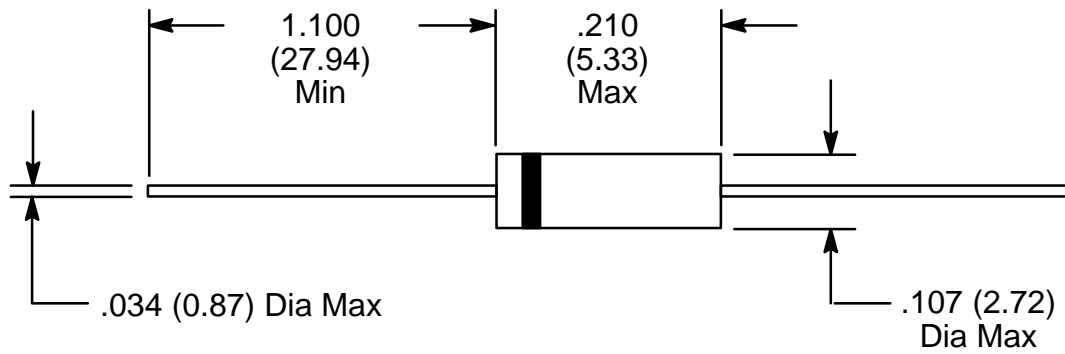
The NTE125 is a general purpose silicon rectifier in a DO41 case designed for low power and switching applications.

Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM}	1000V
Working Peak Reverse Voltage, V_{RWM}	1000V
DC Blocking Voltage, V_R	1000V
Non-Repetitive Peak Reverse Voltage (Halfwave, Single Phase, 60Hz), V_{RSM}	1200V
RMS Reverse Voltage, $V_{R(RMS)}$	700V
Average Rectified Forward Current, I_O (Single Phase, Resistive Load, 60Hz, $T_A = +75^\circ\text{C}$)	1A
Non-Repetitive Peak Surge Current, I_{FSM} (Surge applied at rated load conditions for 1 cycle)	50A
Operating Junction Temperature Range, T_J	-65° to +175°C
Storage Temperature Range, T_{stg}	-65° to +175°C
Maximum Lead Temperature, T_L (During Soldering, 3/8" from case for 10sec at 5lbs tension)	+350°C

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage Drop	v_F	$i_F = 1A, T_J = +25^\circ\text{C}$	–	0.93	1.1	V
Maximum Full-Cycle Average Forward Voltage Drop	$V_{F(AV)}$	$I_O = 1A, T_L +75^\circ\text{C}, 1''$ leads	–	–	0.8	V
Maximum Reverse Current	I_R	$V_{RRM} = 600V, T_J = +25^\circ\text{C}$	–	0.05	10	μA
		$V_{RRM} = 600V, T_J = +100^\circ\text{C}$	–	1.0	50	
Maximum Full-Cycle Average Reverse Current	$I_{R(AV)}$	$I_O = 1A, T_L +75^\circ\text{C}, 1''$ leads	–	–	30	μA



Color Band Denotes Cathode